



# PSMN5R0-80BS

N-channel 80 V, 5.1 mΩ standard level MOSFET in D2PAK

Rev. 1 — 20 March 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

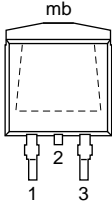
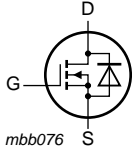
Table 1. Quick reference data

| Symbol                         | Parameter                                    | Conditions   | Min | Typ  | Max | Unit |
|--------------------------------|--|--|-----|------|-----|------|
| $V_{DS}$                       | drain-source voltage                         | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$  | -   | -    | 80  | V    |
| $I_D$                          | drain current                                | $T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$<br>see <a href="#">Figure 1</a>   | [1] | -    | 100 | A    |
| $P_{tot}$                      | total power dissipation                      | $T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>  | -   | -    | 270 | W    |
| $T_j$                          | junction temperature                         |  | -55 | -    | 175 | °C   |
| <b>Static characteristics</b>  |  |  |     |      |     |      |
| $R_{DS(on)}$                   | drain-source on-state resistance             | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 100\text{ °C};$<br>see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a>               | -   | 7.19 | 8.5 | mΩ   |
|                                |  | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$<br>see <a href="#">Figure 12</a>  | -   | 4.36 | 5.1 | mΩ   |
| <b>Dynamic characteristics</b> |  |  |     |      |     |      |
| $Q_{GD}$                       | gate-drain charge                            | $V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 40\text{ V};$<br>see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>              | -   | 21   | -   | nC   |
| $Q_{G(tot)}$                   | total gate charge                            |  | -   | 101  | -   | nC   |
| <b>Avalanche ruggedness</b>    |  |  |     |      |     |      |
| $E_{DS(AL)S}$                  | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$<br>$I_D = 100\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ }\Omega;$<br>unclamped | -   | -    | 396 | mJ   |

[1] Continuous current is limited by package

## 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------------------------|---|---|
| 1   | G      | gate                              |  <p>SOT404 (D2PAK)</p> |  |
| 2   | D      | drain <sup>[1]</sup>              |   |   |
| 3   | S      | source                            |   |   |
| mb  | D      | mounting base; connected to drain |   |   |

[1] It is not possible to make connection to pin 2

## 3. Ordering information

Table 3. Ordering information

| Type number  | Package |  |         |
|--------------|---------|--|---------|
|              | Name    | Description  | Version |
| PSMN5R0-80BS | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

## 4. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| PSMN5R0-80BS | PSMN5R0-80BS |

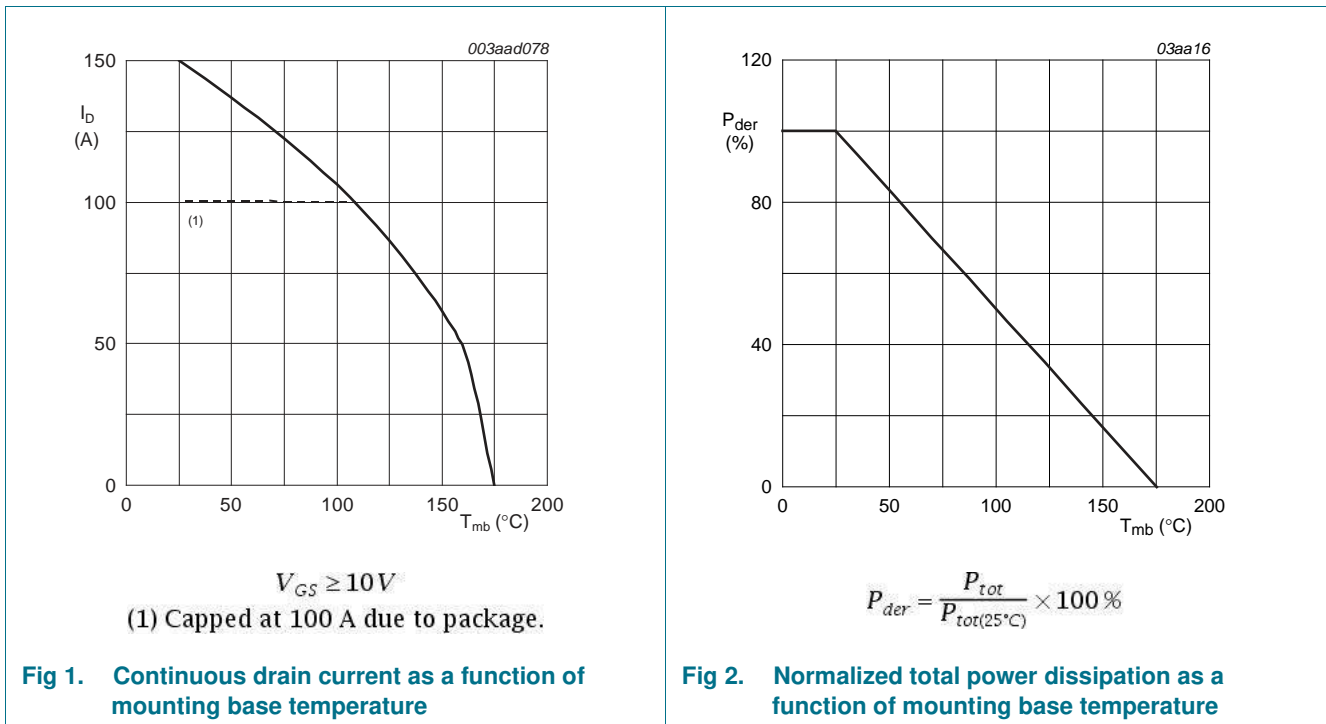
## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions   | Min | Max | Unit |
|-----------------------------|--|--|-----|-----|------|
| $V_{DS}$                    | drain-source voltage                         | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$  | -   | 80  | V    |
| $V_{DGR}$                   | drain-gate voltage                           | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$  | -   | 80  | V    |
| $V_{GS}$                    | gate-source voltage                          |  | -20 | 20  | V    |
| $I_D$                       | drain current                                | $V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>  | [1] | 100 | A    |
|                             |  | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>   | [1] | 100 | A    |
| $I_{DM}$                    | peak drain current                           | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>  | -   | 598 | A    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>   | -   | 270 | W    |
| $T_{stg}$                   | storage temperature                          |  | -55 | 175 | °C   |
| $T_j$                       | junction temperature                         |  | -55 | 175 | °C   |
| $T_{sld(M)}$                | peak soldering temperature                   |  | -   | 260 | °C   |
| <b>Source-drain diode</b>   |  |  |     |     |      |
| $I_S$                       | source current                               | $T_{mb} = 25\text{ °C}$  | [1] | 100 | A    |
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$   | -   | 598 | A    |
| <b>Avalanche ruggedness</b> |  |  |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 100\text{ A}; V_{sup} \leq 80\text{ V}; R_{GS} = 50\text{ }\Omega$ ; unclamped | -   | 396 | mJ   |

[1] Continuous current is limited by package



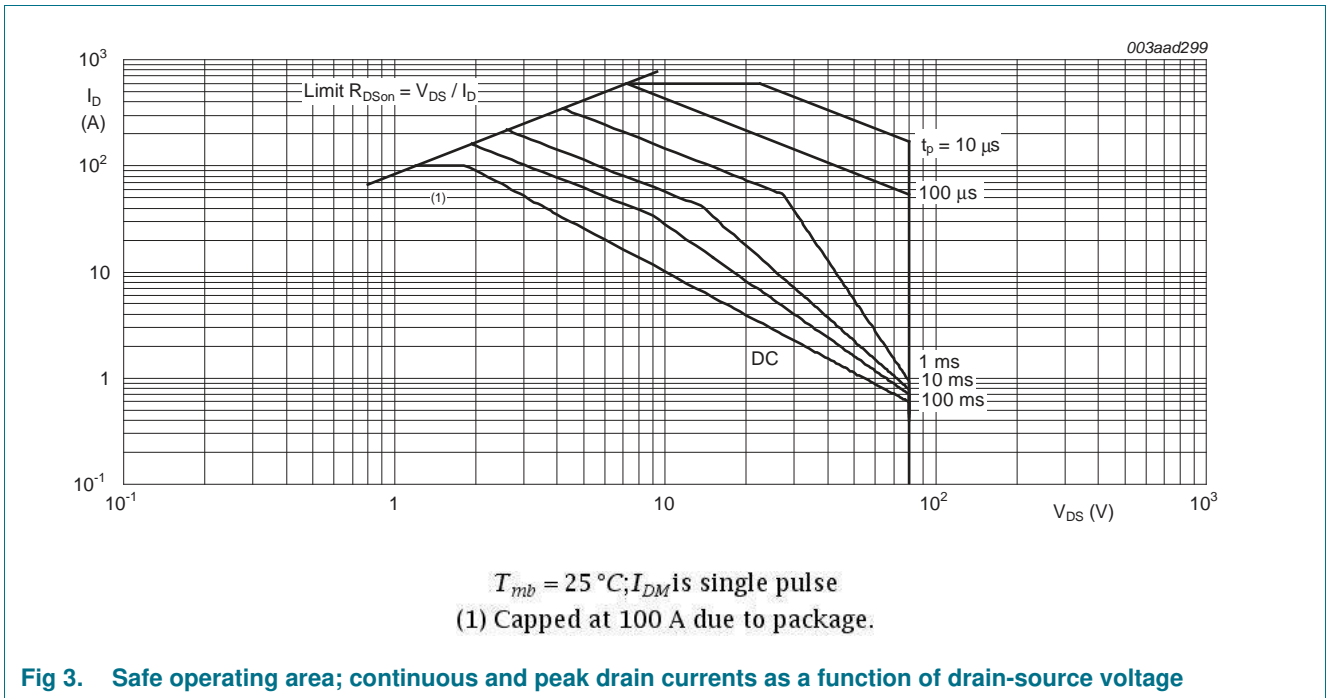
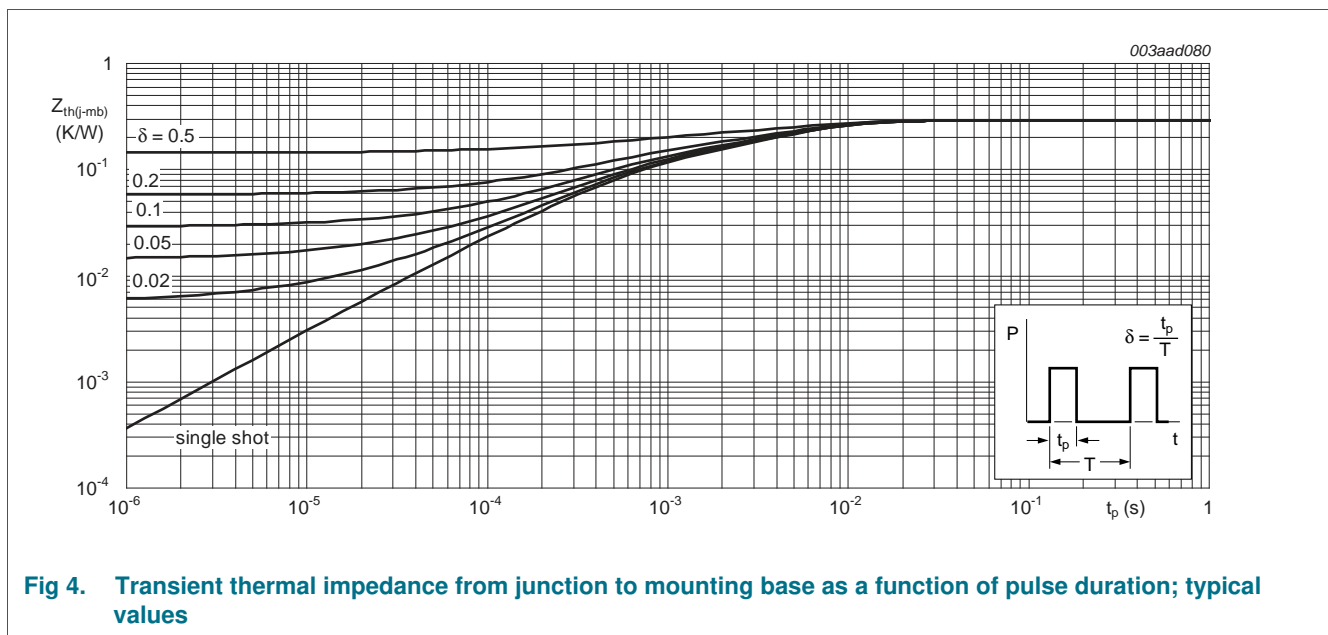


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol         | Parameter   | Conditions  | Min | Typ | Max  | Unit |
|----------------|---|---|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <a href="#">Figure 4</a>                          | -   | 0.3 | 0.56 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 50  | -    | K/W  |



## 7. Characteristics

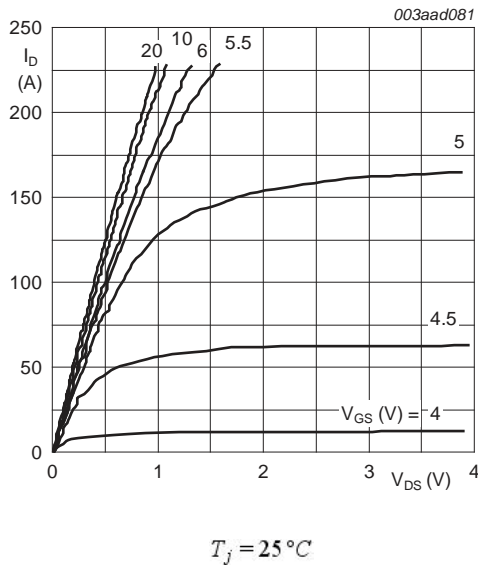
**Table 7. Characteristics**

Tested to JEDEC standards where applicable.

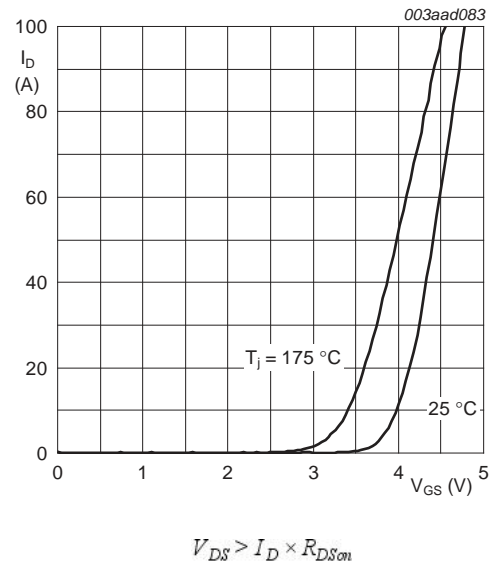
| Symbol                         | Parameter                         | Conditions  | Min | Typ   | Max  | Unit          |
|--------------------------------|-----------------------------------|---|-----|-------|------|---------------|
| <b>Static characteristics</b>  |                                   |   |     |       |      |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage    | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$   | 73  | -     | -    | V             |
|                                |                                   | $I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | 80  | -     | -    | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage     | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 10</a>                                       | 1   | -     | -    | V             |
|                                |                                   | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 10</a>                                       | -   | -     | 4.6  | V             |
|                                |                                   | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 11</a> ; see <a href="#">Figure 10</a>        | 2   | 3     | 4    | V             |
| $I_{DSS}$                      | drain leakage current             | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -   | 0.02  | 8    | $\mu\text{A}$ |
|                                |                                   | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$   | -   | -     | 150  | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current              | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$   | -   | 10    | 100  | nA            |
|                                |                                   | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$  | -   | 10    | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a> | -   | 10.46 | 12.3 | $\Omega$      |
|                                |                                   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 13</a> ; see <a href="#">Figure 12</a> | -   | 7.19  | 8.5  | m $\Omega$    |
|                                |                                   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$<br>see <a href="#">Figure 12</a>                                  | -   | 4.36  | 5.1  | m $\Omega$    |
| $R_G$                          | internal gate resistance (AC)     | $f = 1 \text{ MHz}$   | -   | 0.95  | -    | $\Omega$      |
| <b>Dynamic characteristics</b> |                                   |   |     |       |      |               |
| $Q_{G(tot)}$                   | total gate charge                 | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$  | -   | 87    | -    | nC            |
|                                |                                   | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$<br>see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>            | -   | 101   | -    | nC            |
| $Q_{GS}$                       | gate-source charge                |   | -   | 26    | -    | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge  |   | -   | 18    | -    | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge |   | -   | 8     | -    | nC            |
| $Q_{GD}$                       | gate-drain charge                 |   | -   | 21    | -    | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage       | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$ see <a href="#">Figure 14</a> ;<br>see <a href="#">Figure 15</a>                                   | -   | 4.2   | -    | V             |
| $C_{iss}$                      | input capacitance                 | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$<br>$T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 16</a>           | -   | 6793  | -    | pF            |
| $C_{oss}$                      | output capacitance                |   | -   | 913   | -    | pF            |
| $C_{rss}$                      | reverse transfer capacitance      |   | -   | 350   | -    | pF            |
| $t_{d(on)}$                    | turn-on delay time                | $V_{DS} = 40 \text{ V}; R_L = 0.5 \text{ } \Omega; V_{GS} = 10 \text{ V};$<br>$R_{G(ext)} = 4.7 \text{ } \Omega$                                | -   | 33    | -    | ns            |
| $t_r$                          | rise time                         |   | -   | 21    | -    | ns            |
| $t_{d(off)}$                   | turn-off delay time               |   | -   | 73    | -    | ns            |
| $t_f$                          | fall time                         |   | -   | 14    | -    | ns            |

**Table 7. Characteristics ...continued**  
Tested to JEDEC standards where applicable.

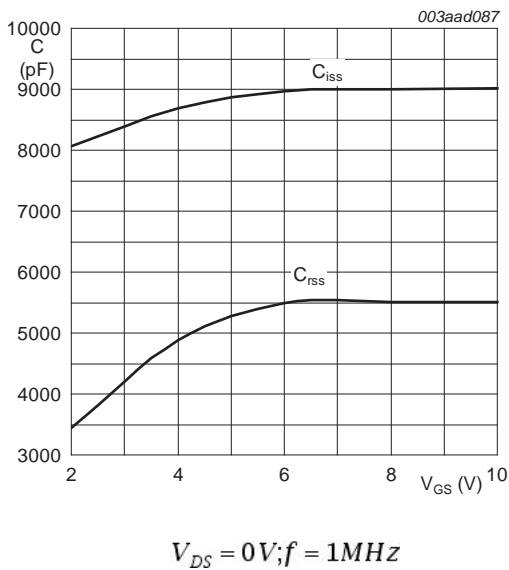
| Symbol                    | Parameter             | Conditions  | Min | Typ | Max | Unit |
|---------------------------|-----------------------|---|-----|-----|-----|------|
| <b>Source-drain diode</b> |                       |   |     |     |     |      |
| $V_{SD}$                  | source-drain voltage  | $I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ;<br>see <a href="#">Figure 17</a> | -   | 0.8 | 1.2 | V    |
| $t_{rr}$                  | reverse recovery time | $I_S = 25\text{ A}$ ; $di_S/dt = 100\text{ A}/\mu\text{s}$ ;  | -   | 56  | -   | ns   |
| $Q_r$                     | recovered charge      | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 40\text{ V}$  | -   | 116 | -   | nC   |



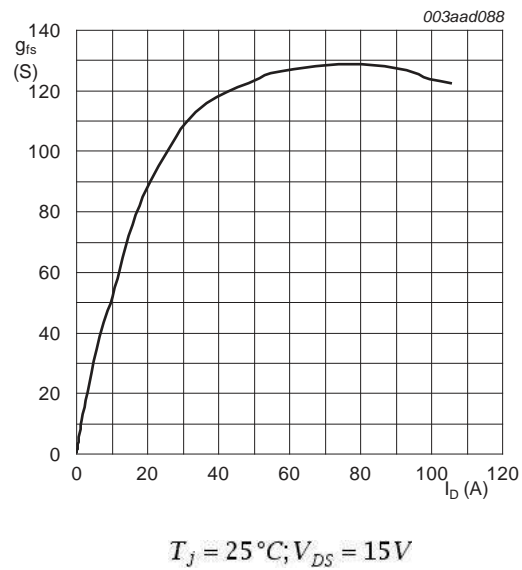
**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



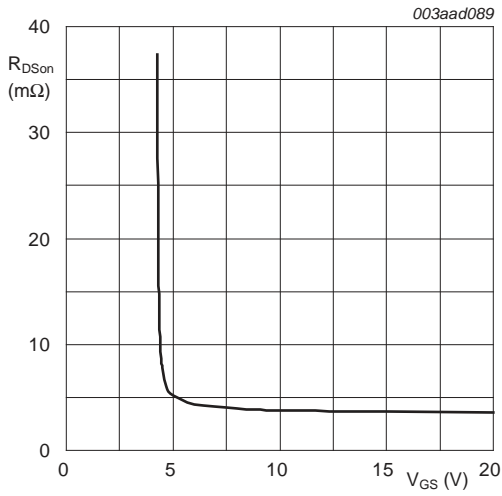
**Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



**Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values**

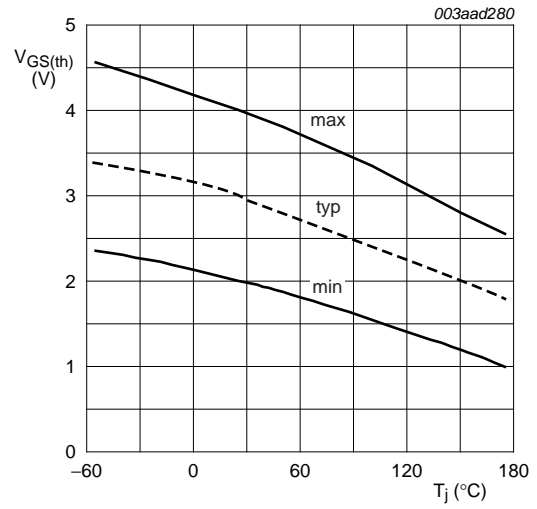


**Fig 8. Forward transconductance as a function of drain current; typical values**



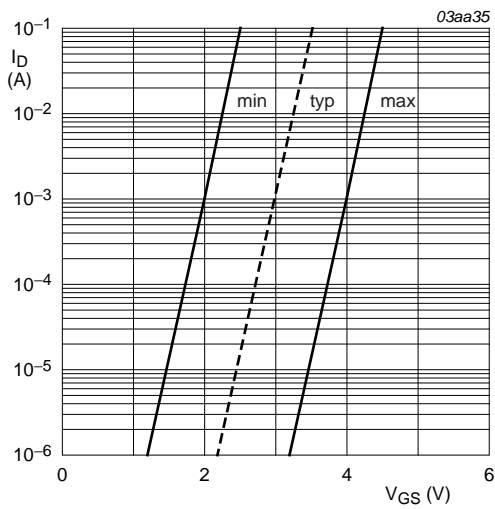
$T_j = 25^\circ C; I_D = 25A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



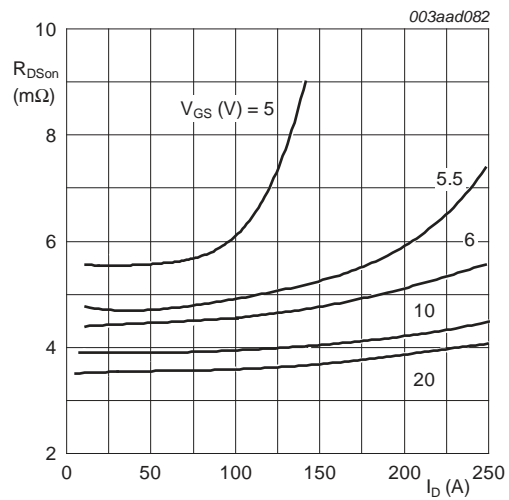
$I_D = 1 mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$T_j = 25^\circ C; V_{DS} = 5V$

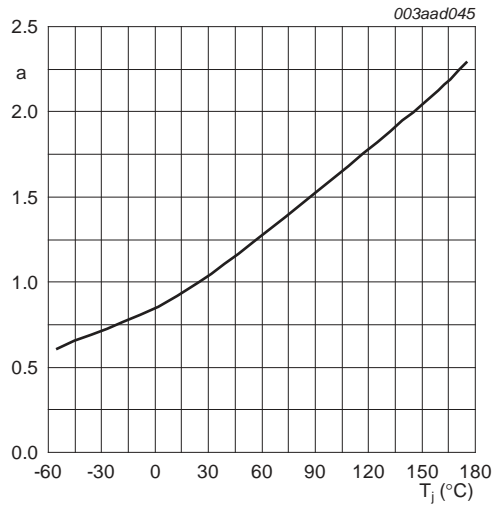
Fig 11. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25^\circ C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values





$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^{\circ}\text{C})}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

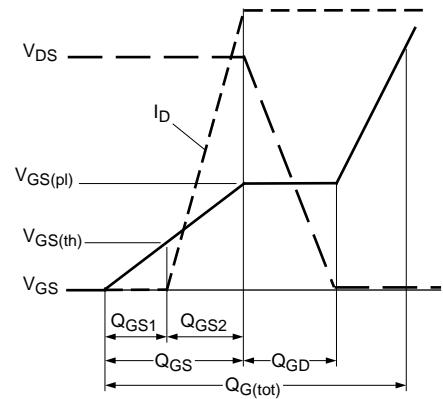
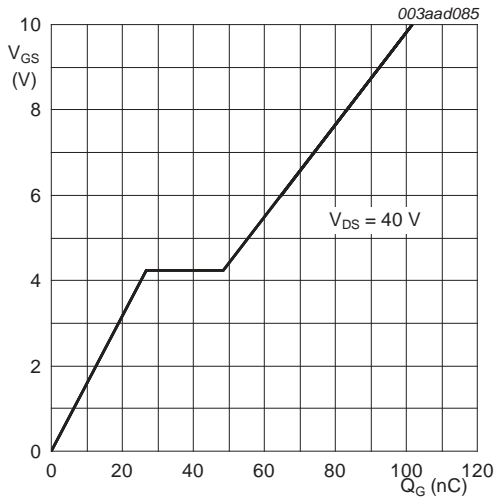
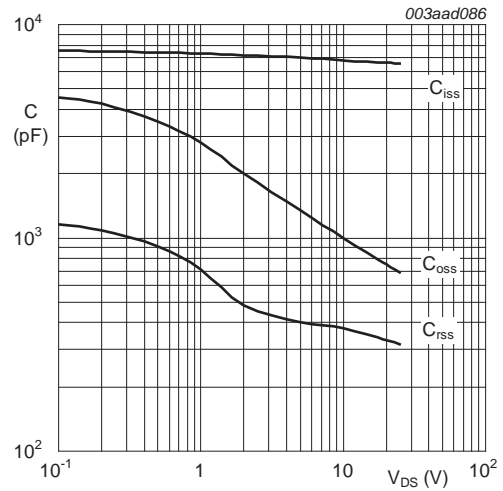


Fig 14. Gate charge waveform definitions



$$T_j = 25^{\circ}\text{C}; I_D = 25\text{A}$$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

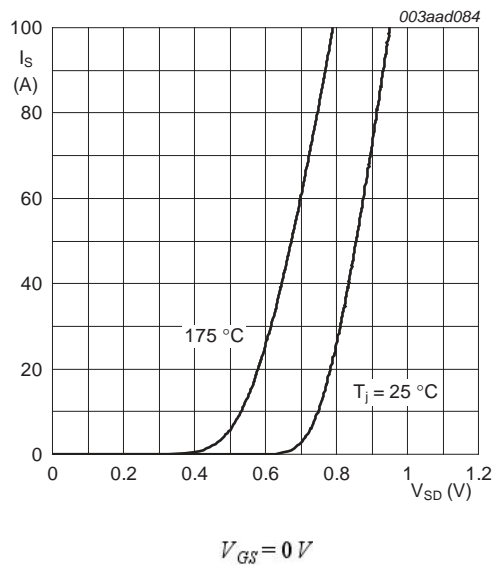


Fig 17. Source current as a function of source-drain voltage; typical values

8. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404

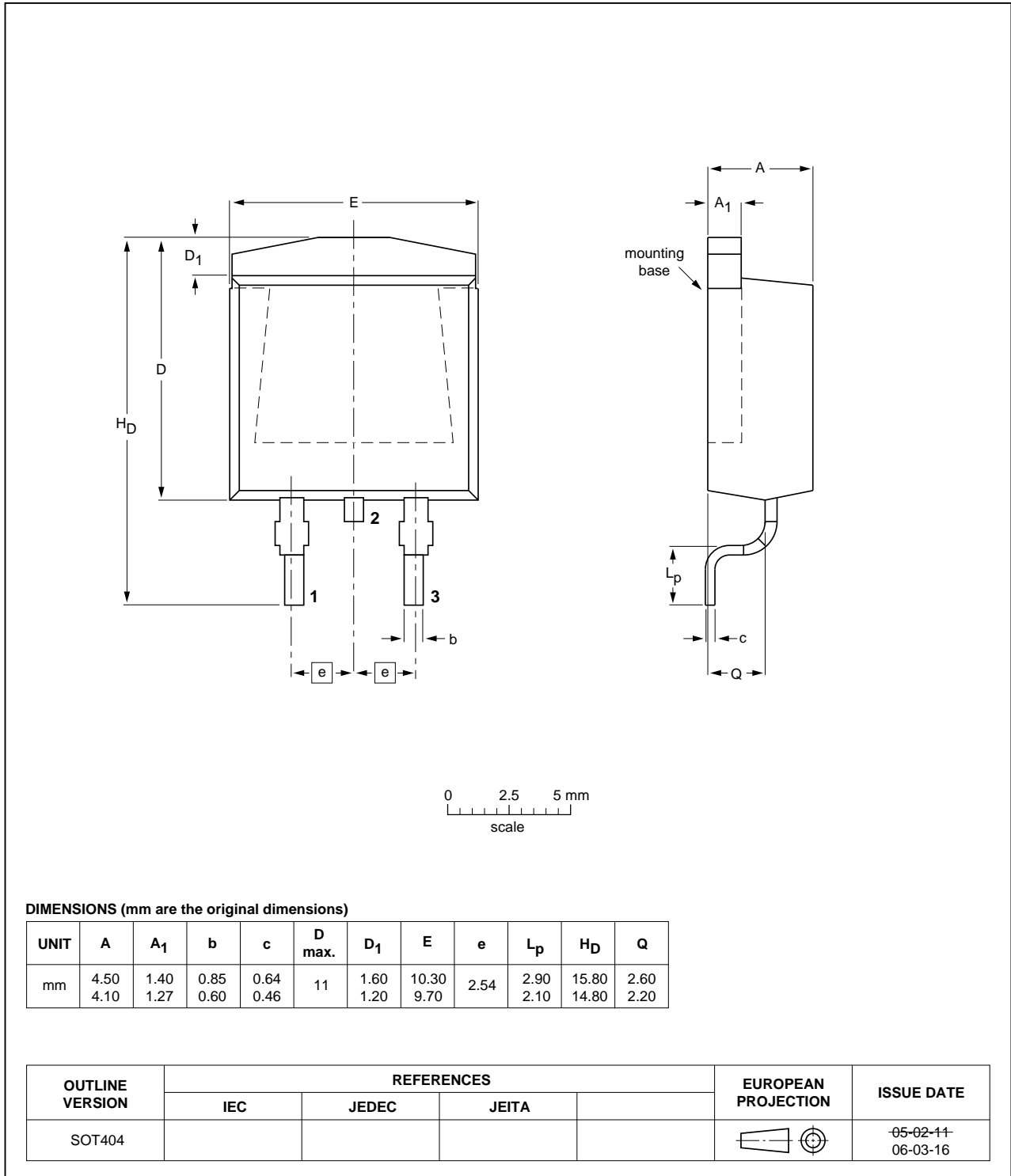


Fig 18. Package outline SOT404 (D2PAK)

## 9. Revision history

Table 8. Revision history

| Document ID      | Release date | Data sheet status  | Change notice | Supersedes |
|------------------|--------------|--------------------|---------------|------------|
| PSMN5R0-80BS v.1 | 20120320     | Product data sheet | -             | -          |

## 10. Legal information

### 10.1 Data sheet status

| Document status <sup>[1]</sup> [2] | Product status <sup>[3]</sup> | Definition  |
|------------------------------------|-------------------------------|---|
| Objective [short] data sheet       | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet     | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet         | Production                    | This document contains the product specification.                                     |

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product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

## 10.4 Trademarks

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## 11. Contact information

For more information, please visit: <http://www.nexperia.com>

For sales office addresses, please send an email to: [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)

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